

NE5550279A

Silicon Power LDMOS FET

FEATURES

- High Output Power
- : $P_{out} = 33.0 \text{ dBm TYP}$. ($V_{DS} = 7.5 \text{ V}$, $I_{Dset} = 40 \text{ mA}$, f = 460 MHz, $P_{in} = 15 \text{ dBm}$)
- High power added efficiency
 - $: \eta_{add} = 68\% \text{ TYP.} (V_{DS} = 7.5 \text{ V}, I_{Dset} = 40 \text{ mA}, f = 460 \text{ MHz}, P_{in} = 15 \text{ dBm})$ $: G_L = 22.5 \text{ dB TYP.} (V_{DS} = 7.5 \text{ V}, I_{Dset} = 40 \text{ mA}, f = 460 \text{ MHz}, P_{in} = 0 \text{ dBm})$
- High Linear gainHigh ESD tolerance
- Suitable for VHF to UHF-BAND Class-AB power amplifier.

APPLICATIONS

- 150 MHz Band Radio System
- 460 MHz Band Radio System
- 900 MHz Band Radio System

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
NE5550279A	NE5550279A-A	79A	W7	 12 mm wide embossed taping
		(Pb Free)		Gate pin faces the perforation side of the tape
NE5550279A-T1	NE5550279A-T1-A			 12 mm wide embossed taping
				Gate pin faces the perforation side of the tape
				Qty 1 kpcs/reel
NE5550279A-T1A	NE5550279A-T1A-A			12 mm wide embossed taping
				Gate pin faces the perforation side of the tape
				Qty 5 kpcs/reel

Remark To order evaluation samples, please contact your nearby sales office. Part number for sample order: NE5550279A-A

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$, unless otherwise specified)

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V _{DS}	30	V
Gate to Source Voltage	V _{GS}	6.0	V
Drain Current	I _{DS}	0.6	А
Drain Current (50% Duty Pulsed)	I _{DS-pulse}	1.2	A
Total Power Dissipation Note	P _{tot}	6.25	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T _{stg}	–55 to +150	°C

Note: Value at $T_C = 25^{\circ}C$

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.



Data Sheet R09DS0033EJ0200 Rev.2.00 Jul 04, 2012



RECOMMENDED OPERATING RANGE (T_A = 25^{\circ}C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V _{DS}		-	7.5	9.0	V
Gate to Source Voltage	V _{GS}		1.65	2.20	2.85	V
Drain Current	I _{DS}		-	0.4	-	Α
Input Power	Pin	f = 460 MHz, V _{DS} = 7.5 V	-	15	20	dBm

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Gate to Source Leakage Current	I _{GSS}	V _{GS} = 6.0 V	-	-	100	nA
Drain to Source Leakage Current	I _{DSS}	V _{DS} = 25 V	-	- 7	10	μA
(Zero Gate Voltage Drain Current)						
Gate Threshold Voltage	V _{th}	$V_{DS} = 7.5 \text{ V}, I_{DS} = 1.0 \text{ mA}$	1.15	1.65	2.25	V
Drain to Source Breakdown Voltage	BV _{DSS}	I _{DS} = 10 μA	25	38	_	V
Transconductance	G _m	$V_{DS} = 7.5 \text{ V}, I_{DS} = 140\pm20 \text{ mA}$	0.36	0.44	0.58	S
Thermal Resistance	R _{th}	Channel to Case		20.0	_	°C/W
RF Characteristics						
Output Power	Pout	$f = 460 \text{ MHz}, V_{DS} = 7.5 \text{ V},$	31.5	33.0	-	dBm
Drain Current	I _{DS}	P _{in} = 15 dBm,		0.38	_	А
Power Drain Efficiency	η_{d}	I _{Dset} = 40 mA (RF OFF)	_	70	_	%
Power Added Efficiency	η_{add}		_	68	-	%
Linear Gain	G_L^{Note}		_	22.5	—	dB

Note: $P_{in} = 0 \text{ dBm}$

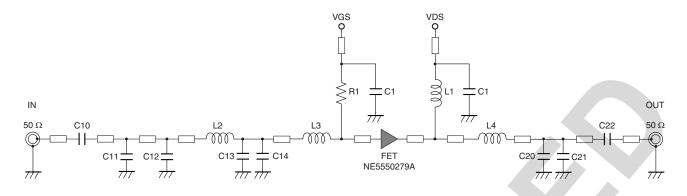
<R>

Remark DC performance is 100% testing. RF performance is testing several samples per wafer. Wafer rejection criteria for standard devices is 1 reject for several samples.





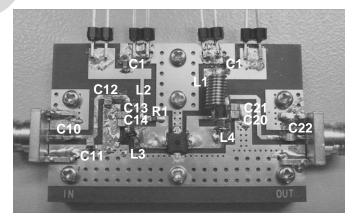
TEST CIRCUIT SCHEMATIC FOR 460 MHz



COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

Symbol	Value	Туре	Maker		
C1	1 <i>μ</i> F	GRM188B31C105KA92	Murata		
C10	22 pF	GRM1882C1H220JA01	Murata		
C11	1.2 pF	ATC100A1R2JW	American Technical		
			Ceramics		
C12	4.7 pF	ATC100A4R7BW	American Technical		
			Ceramics		
C13	15 pF	ATC100A150BW	American Technical		
			Ceramics		
C14	12 pF	ATC100A120BW	American Technical		
		· · · ·	Ceramics		
C20	10 pF	ATC100A100JW	American Technical		
			Ceramics		
C21	3.9 pF	ATC100A3R9BW	American Technical		
			Ceramics		
C22	100 pF	ATC100A101JW	American Technical		
			Ceramics		
R1	2 kΩ	1/10 W Chip Resistor	KOA		
		RK73B1JTTD202J			
L1	123 nH	ϕ 0.5 mm, ϕ D = 3 mm, 10 Turns	Ohesangyou		
L2	10 nH	LQW18AN10NG00	Murata		
L3	9.8 nH	$\phi 0.4 \text{ mm}, \phi D = 1.6 \text{ mm}, 3 \text{ Turns}$	Ohesangyou		
L4	20 nH	$\phi 0.5 \text{ mm}, \phi \text{D} = 3 \text{ mm}, 2 \text{ Turns}$	Ohesangyou		
PCB	-	R4775, t = 0.4 mm, <i>ε</i> r = 4.5, size = 30 × 48 mm	Panasonic		
SMA Connecter		WAKA 01K0790-20	WAKA		

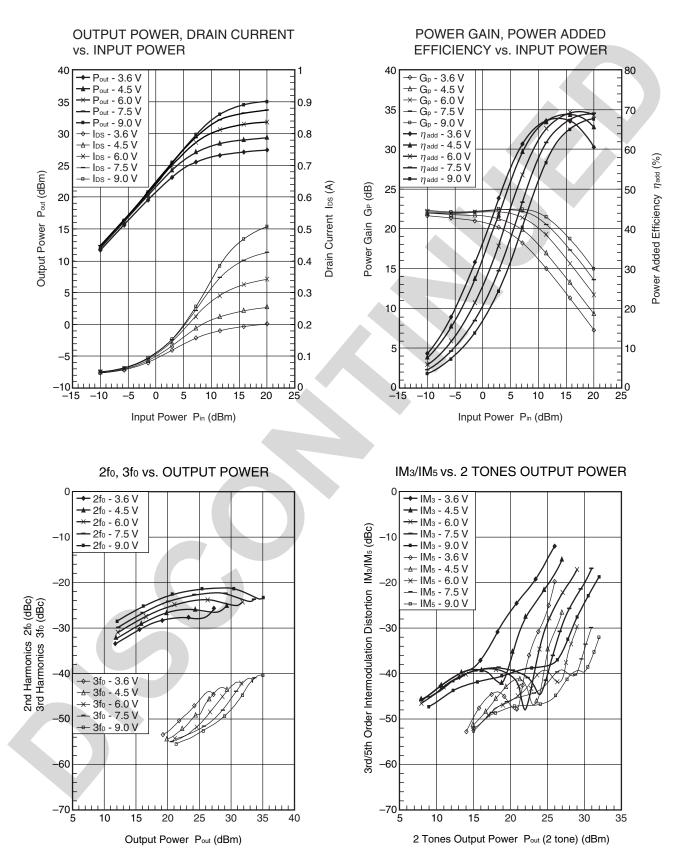
COMPONENT LAYOUT OF TEST CIRCUIT FOR 460 MHz





TYPICAL CHARACTERISTICS 1 ($T_A = 25^{\circ}C$)

- R: f = 460 MHz, $V_{DS} = 3.6/4.5/6/7.5/9 \text{ V}$, $I_{Dset} = 40 \text{ mA}$, $P_{in} = -10 \text{ to } 20 \text{ dBm}$
- IM: f1 = 460 MHz, f2 = 461 MHz, V_{DS} = 3.6/4.5/6/7.5/9 V, I_{Dset} = 40 mA, P_{out} (2 tone) = 8 to 32 dBm



Remark The graphs indicate nominal characteristics.





S-PARAMETERS

S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

Click here to download S-parameters.

 $[Products] \rightarrow [RF \ Devices] \rightarrow [Device \ Parameters]$

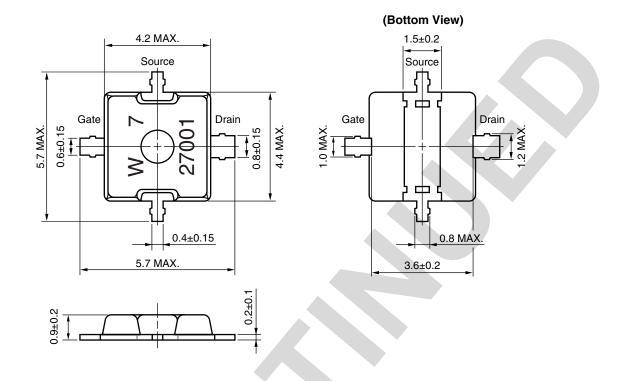
URL http://www.renesas.com/products/microwave/



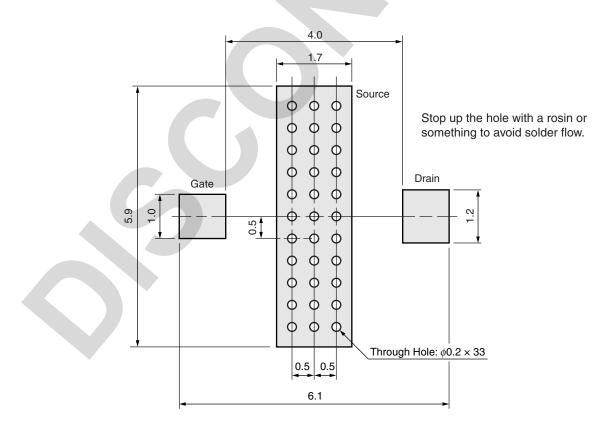


PACKAGE DIMENSIONS

79A (UNIT: mm)



79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)







RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature)	: 260°C or below	IR260
	Time at peak temperature	: 10 seconds or less	
	Time at temperature of 220°C or higher	: 60 seconds or less	
	Preheating time at 120 to 180°C	: 120±30 seconds	
	Maximum number of reflow processes	: 3 times	
	Maximum chlorine content of rosin flux (% mass)	: 0.2% (Wt.) or below	
Wave Soldering	Peak temperature (molten solder temperature)	: 260°C or below	WS260
	Time at peak temperature	: 10 seconds or less	
	Preheating temperature (package surface temperature)		
	: 120°C or below		
	Maximum number of flow processes	: 1 time	
	Maximum chlorine content of rosin flux (% mass)	: 0.2% (Wt.) or below	
Partial Heating	Peak temperature (terminal temperature)	: 350°C or below	HS350
	Soldering time (per side of device)	: 3 seconds or less	
	Maximum chlorine content of rosin flux (% mass)	: 0.2% (Wt.) or below	r

CAUTION

Do not use different soldering methods together (except for partial heating).



Revision History

NE5550279A Data Sheet

		Description		
Rev.	Date	Page Summary		
1.00	Mar 28, 2012	_	First edition issued	
2.00	Jul 04, 2012	p.2	Modification of ELECTRICAL CHARACTERISTICS	

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